

FOR IMMEDIATE RELEASE

No. 2376

Product Inquiries

Hideyuki Oto
High Frequency & Optical Semiconductor
Overseas Marketing Department
Tel +81-72-780-3835
Oto.Hideyuki@ak.MitsubishiElectric.co.jp
<http://www.mitsubishichips.com/>

Media Contact

Travis Woodward
Public Relations Department
Mitsubishi Electric Corporation
Tel: +81-3-3218-3380
Travis.Woodward@eb.MitsubishiElectric.co.jp
<http://global.mitsubishielectric.com/news/>

**MITSUBISHI ELECTRIC ANNOUNCES SALE OF LOW NOISE GaAs
HEMT 'MGF4934AM'**

Tokyo, December 6, 2005 – Mitsubishi Electric Corporation (President and CEO: Tamotsu Nomakuchi) announced today it has developed a high gain version of a 4 pin flat lead plastic mold package HEMT¹, highly suitable for low noise amplifiers in 12 GHz-band satellite broadcasting reception systems. Shipment will begin in December 2005.

¹ HEMT- High Electron Mobility Transistor

Sale Summary

Product	Model	Characteristic	Price	Release Date	Amount	Comment
Low Noise GaAs HEMT	MGF4934AM	NF : 0.6dB Gs : 12.5dB (f=12GHz) Gain improves by 1dB compared to our previous models	Sample price \$0.2	Dec. 20, 2005	2 million /month	Suitable for the latter stages of low noise amplifier of DBS converter

Aim of Sale

These transistors will mainly be used in the Direct Broadcast Satellite (DBS) market for low noise amplifiers in DBS converters. While current satellite broadcast systems have developed many different functions such as multi-satellite reception and Digital/High Definition broadcasts, price reductions are also continuing, and demand for HEMT has increased accordingly. The market is demanding a low price device structure capable of being mass-produced and high gain / low noise characteristics at high frequencies for the Digital broadcasts system.

Mitsubishi Electric responded to this market demand last year by creating a 4-pin flat lead plastic mold package HEMT for mass-production. With this new HEMT, we have developed a transistor with 1 dB gain

over previous HEMT. This was done by using a process that reduces parasitic capacity by adopting a low dielectric constant film formation.

Product Characteristics

1 db transmission gain over previous HEMT

By adopting a low dielectric constant film, NF (noise figure) =0.6 dB, Gs (associated gain) =12.5 dB (f=12GHz, typical value), and we achieved a 1 dB gain over previous HEMT.

Features

- Recommended bias condition : VDS=2V、ID=10mA
- Noise figure (NFmin.) : 0.6dB (f=12GHz, typical)
- Associated gain (Gs) : 12.5dB (f=12GHz, typical)

Use of standard 4 pin flat lead package

An unchanged foot pattern from previous HEMT will make new product substitution easy.

About Mitsubishi Electric

With over 80 years of experience in providing reliable, high-quality products to both corporate clients and general consumers all over the world, Mitsubishi Electric Corporation (TSE:6503) is a recognized world leader in the manufacture, marketing and sales of electrical and electronic equipment used in information processing and communications, space development and satellite communications, consumer electronics, industrial technology, energy, transportation and building equipment. The company recorded consolidated group sales of 3,410 billion yen (US\$ 31.9billion*) in the fiscal year ended March 31, 2005. For more information visit <http://global.mitsubishielectric.com>

*At an exchange rate of 107 yen to the US dollar, the rate given by the Tokyo Foreign Exchange Market on March 31, 2005.

###